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Amendments to the Claims

1. (*Original*) A method of manufacturing a semiconductor device comprising the step of depositing an epitaxial layer based on Group IV elements on a silicon substrate by Chemical Vapor Deposition, and including employing nitrogen or a noble gas as a carrier gas.
2. (*Original*) A method as claimed in claim 1, which is employed to form an epitaxial layer based on silicon, germanium and/or carbon.
3. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises $\text{Si}_{1-y}\text{C}_y$.
4. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises a SiGe epitaxial layer.
5. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$.
6. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises a silicon epitaxial layer.
7. (*Original*) A method as claimed in any one of the preceding claims, which is carried out at a low temperature.
8. (*Original*) A method as claimed in claim 7, which is carried out at a temperature of less than about 600°C.
9. (*Currently Amended*) Chemical Vapor Deposition apparatus ~~(10)~~ comprising a chamber ~~(12)~~ having a gas input port ~~(14)~~ and a gas output port ~~(16)~~, and means ~~(18)~~ for mounting a silicon substrate ~~(20)~~ within the chamber ~~(12)~~, said apparatus ~~(10)~~ further including a gas source ~~(24)~~ connected to the input port ~~(14)~~ and arranged to provide nitrogen or a noble gas as a carrier gas.

10. (*Currently Amended*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in ~~any one of claims 2-8.~~
claim 2.

10. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 3.

11. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 4.

12. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 5.

13. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 6.

14. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 7.

15. (*New*) Apparatus as claimed in claim 9, which is arranged to deposit an epitaxial layer in accordance with the method as claimed in claim 8.